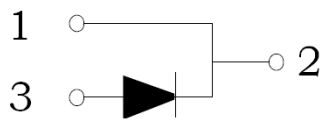


TO-220AC

Ultrafast Recovery Diode in a TO-220AC Plastic Package.

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

For high frequency, high voltage, high current rectifier diode, freewheeling diode.



PIN1 2 Cathode

PIN 3 Anode

See Marking Instructions

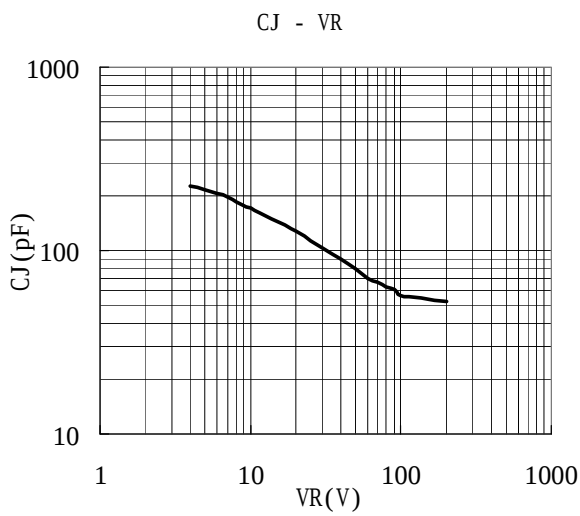
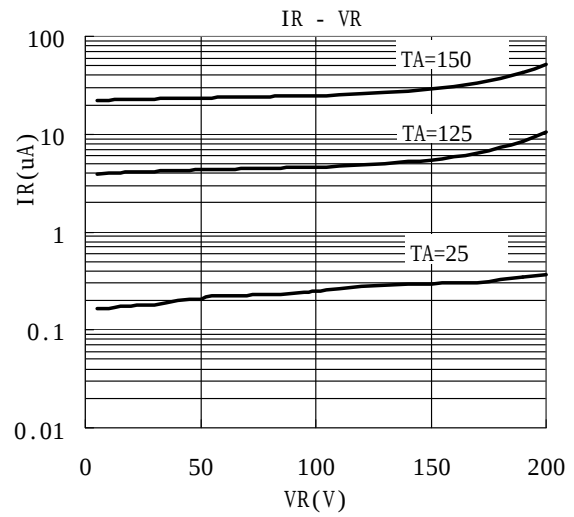
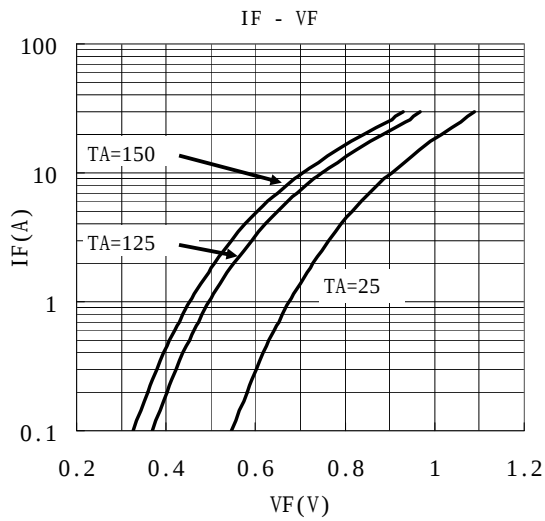
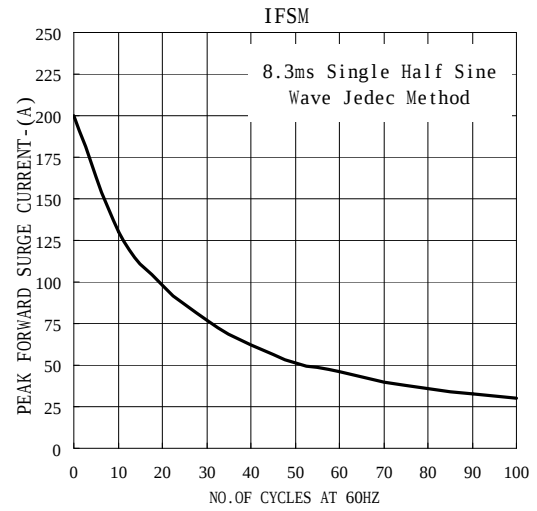
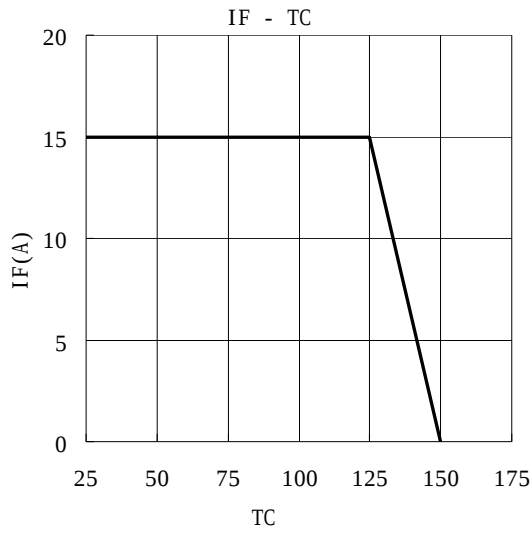
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
RMS Voltage	V_{RMS}	140	V
DC Blocking Voltage	V_{DC}	200	V
Average Forward Current	I_F	1×15	A
Peak forward surge current	I_{FSM}	200	A
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	1.5	$^{\circ}C/W$
Junction Temperature Range	T_J	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 150	$^{\circ}C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R=1mA$	200			V
Forward Voltage	V_F	$I_F=3.0A \quad T_C=25$		0.76	0.85	V
		$I_F=3.0A \quad T_C=150$		0.55	0.65	
		$I_F=15A \quad T_C=25$			1.05	
		$I_F=15A \quad T_C=150$			0.85	
Instantaneous Reverse Current(Note1)	I_R	$V_R=200V \quad T_a=25$			10	μA
		$V_R=140V \quad T_a=150$			100	
		$V_R=200V \quad T_a=150$			500	
Reverse Recovery Time	t_{rr}	$I_F=0.5A \quad I_R=1.0A, \quad I_{RR}=0.25A$			35	ns

/Notes

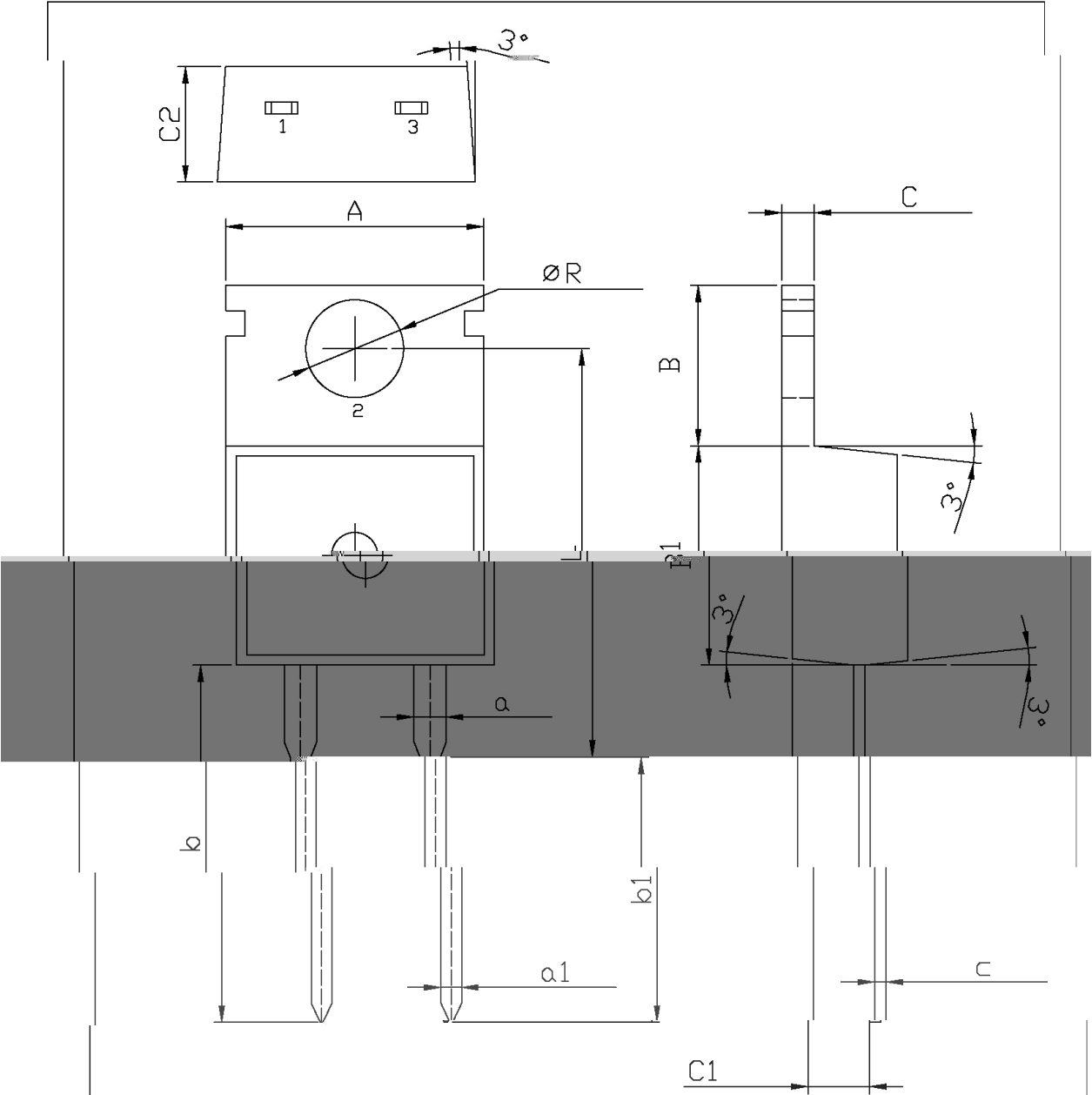
1. /Short duration pulse test used to minimize self-heating effect.

2. / Unless otherwise noted, values for the parameters of a single chip

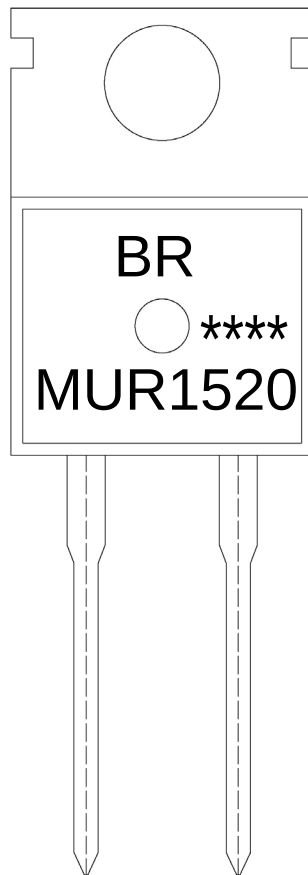


TO-220AC

Unit:mm



Dimensions In Millimeters			Dimensions In Millimeters		
Symbol	Min	Max	Symbol	Min	Max
A	9.8	10.2	B	6.3	6.7
R	3.56	3.64	B1	9.0	9.4



BR

MUR1520

Note:

BR:

Company Code

MUR1520

Product Type.

****:

Lot No. Code, code change with Lot No.

